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		or ("5335240") or ("5998298")).PN.	USPAT;	2003/04/17 17:47
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		and stack\$4	USPAT;	2003/04/15 18:35
		and bodony i	US-PGPUB;	
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	4		DERWENT; IBM TDB	
-	643	photonic and semiconductor and substrate	USPAT;	2002/04/15 14:41
		and stack\$4	US-PGPUB	2003/04/15 14:41
-	4.	photonic and semiconductor and substrate	EPO; JPO;	2003/04/15 14:41
İ		and stack\$4	DERWENT;	2003/04/15 14:41
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1 -	406	photonic and semiconductor and substrate	USPAT;	2003/04/15 14:43
		and stack\$4 and dielectric and material	US-PGPUB	2003/04/15 14:43
-	27	359/321 and photonic and semiconductor and	USPAT;	2003/04/15 18:41
		substrate	US-PGPUB;	2003/04/15 18:41
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		substrate	US-PGPUB;	
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		substrate	US-PGPUB;	<u> </u>
r			EPO; JPO;	
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-	9	359/587 and photonic and semiconductor and	IBM_TDB USPAT;	2002/04/15 10 40
	1.1	substrate	US-PGPUB;	2003/04/15 18:48
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		and substrate	US-PGPUB;	
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	55	substrate	USPAT;	2003/04/15 19:59
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-	176	372/45 and photonic and semiconductor and	USPAT;	2003/04/24 14:17
	·	substrate	US-PGPUB;	2000/04/24 14:1/
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-	0	372/451 and photonic and semiconductor and	USPAT;	2003/04/15 21:24
		substrate	US-PGPUB;	
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Or band\$(qap\$2))			1	dielectric) and (photonic add (crystals)		2003/04/17 17:50
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45	-			or band\$1gap\$2))	EPO; JPO;	1
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-	128	photonic.ti. and forming and etching	USPĀT;	2003/04/24 12:46
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*		Photonic near (crystal or bandgap)	US-PGPUB	
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		substrate	US-PGPUB;	1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2
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,	,	substrate	US-PGPUB;	
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-	58	Fire sourie and semiconductor and	USPAT;	2003/04/24 14:26
		substrate ,	US-PGPUB;	
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		and photonic and semiconductor and	US-PGPUB;	
	Í	substrate	EPO; JPO;	
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-	71	359/322,245,250,321,327,238,226,332,248.ccl	SUSPAT;	2003/04/24 15:16
		and photonic and semiconductor and	US-PGPUB	
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-	263	photonic and semiconductor and (plurality	USPAT	2004/05/19 19:00
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-	1	KOSCIELNIAK.in. and WACLAW	US-PGPUB;	2004/05/19 19:21
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